• Crystal truncation rods

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Homework Assignment #04: Chapter 4: 2, 4, 6, 7, 10 due Tuesday, March 10, 2020



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C. Segre (IIT)



Magnetite,  $Fe_3O_4$ , is a technologically important material for environmental remediation

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There are two possible surfaces, the oxygen octahedral iron, OOI (a), and the oxygen mixed-iron, OMI (b), terminations

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# Magnetite (111) surface

Crystal truncation rod measurements require an oriented single crystal with a polished and cleaned surface.



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The final polished surface has clear terraces of between 150 Å–700 Å and a surface roughness of about 1.4 Å as seen in the inset from the atomic force microscopy images

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## CTR data and modeling



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The result of the modeling of the CTR data indicates that the surface is 75% OOI and 25% OMI

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The modeling also can provide details about the distance changes in the first layers at the surface

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"Critical role of a buried interface in the Stranski-Krastanov growth of metallic nanocrystals: Quantum size effects in  $Ag/Si(111)-(7 \times 7)$ ," Y. Chen et al. *Phys. Rev. Lett.* **114**, 035501 (2015).

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A Si(111) crystal is placed in an ultra-high vacuum chamber and flash-annealed to clean and reconstruct the surface

Ag was thermally evaporated on the surface and both reflectivity measurements of the surface and CTR measurements of the Ag (001) growth layer were performed



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Reflectivity "sees" the entire surface while CTR measures only the incommensurate Ag crystalline layer on the surface

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Modeling shows that the islands are displaced from the surface

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PHYS 570 - Spring 2020

March 03, 2020 8 / 22



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Depositions as a function of temperature show that the island height distribution increases and broadens due to mobility of Ag atoms

The exceptional stability of the three layer islands is consistent with quantum confinement effects that drive the growth process

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The islands thus have a weak interaction with the substrate compared to the wetting layer

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the diffraction pattern has main Bragg peaks plus satellite peaks

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If the modulation of the structure is a multiple of the lattice parameter, the modulation is simply a superlattice and the actual lattice parameter will be changed.



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In 2011 Shechtman was awarded the Nobel Prize in Chemistry

C. Segre (IIT)

PHYS 570 - Spring 2020

The electron micrographs show that there must be long range order to be able to get such sharp diffraction peaks



"Metallic phase with long-range orientational order and no translational symmetry," D. Shechtman, I. Blech, D. Gratias, and J.W. Cahn, *Phys. Rev. Lett.* 53, 1951-1953 (1984)

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The 5-fold symmetry is evident in the 10 spots surrounding the center of the left image and the pentagonal arrangements of atoms in the image on the right.



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Other groups have discovered stable icosahedral phases with three and two elements.

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# Quasicrystal diffraction patterns

The  $AI_{65}Cu_{20}Fe_{15}$  system was one of the first stable quasicrystals to be discovered. Later discovery of stable quasicrystals in the Ta-Te, Cd-Ca, and Cd-Yb systems enabled large crystals to be grown.

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For a 1D lattice, we replace the position of the atom with its *instantaneous* position,  $\vec{R}_n + \vec{u}_n$  where  $\vec{u}_n$  is the displacement from the equilibrium position,  $\vec{R}_n$ .

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Substituting into the expression for intensity

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$$+ \sum_{m} \sum_{n} f(\vec{Q}) e^{-M} e^{i\vec{Q}\cdot\vec{R}_{m}} f^{*}(\vec{Q}) e^{-M} e^{-i\vec{Q}\cdot\vec{R}_{n}} \left[ e^{Q^{2}\langle u_{Qm}u_{Qn}\rangle} - 1 \right]$$

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The first term is just the elastic scattering from the lattice with the addition of the term  $e^{-M} = e^{-Q^2 \langle u_Q^2 \rangle/2}$ , called the Debye-Waller factor.

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The second term is the Thermal Diffuse Scattering and actually increases with mean squared displacement.

C. Segre (IIT)

PHYS 570 - Spring 2020

$$I^{TDS} = \sum_{m} \sum_{n} f(\vec{Q}) e^{-M} e^{i\vec{Q}\cdot\vec{R}_{m}} f^{*}(\vec{Q}) e^{-M} e^{-i\vec{Q}\cdot\vec{R}_{n}} \left[ e^{Q^{2} \langle u_{Qm}u_{Qn} \rangle} - 1 \right]$$

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The TDS has a width determined by the correlated displacement of atoms which is much broader than a Bragg peak.

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M. Holt, et al. Phys. Rev. Lett. 83, 3317 (1999).

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For crystals with several different types of atoms, we generalize the unit cell scattering factor.

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for isotropic atomic vibrations

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In general, Debye-Waller factors can be anisotropic

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$$B_{\mathcal{T}}[\text{\AA}^2] = \frac{11492\text{T}[\text{K}]}{\text{A}\Theta^2[\text{K}^2]}\phi(\Theta/\text{T}) + \frac{2873}{\text{A}\Theta[\text{K}]}$$

Energy





 $egin{aligned} B_{\mathcal{T}} &= rac{11492\,T}{A\Theta^2}\phi(\Theta/T) \ &+ rac{2873}{A\Theta} \end{aligned}$ 

	Α	Θ	B <sub>4.2</sub>	B <sub>77</sub>	B <sub>293</sub>	
		(K)		$(Å^2)$		
C*	12	2230	0.11	0.11	0.12	
AI	27	428	0.25	0.30	0.72	
Cu	63.5	343	0.13	0.17	0.47	
*diamond						

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	~	U	D4.2	D//	D293	
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# Powder diffraction

(a) Ambient pressure

